Product data sheet

1. General description

Hyperfast power diode in a TO263 (D2PAK) plastic package.

2. Features and benefits

- Fast switching
- Low leakage current
- · Low reverse recovery current
- Reduces switching losses in associated MOSFET

3. Applications

- Server power supplies
- Telecom power supplies
- EV charger
- Air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _R	reverse voltage	DC	-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 101 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	30	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; $T_{mb} \le$ 101 °C; square-wave pulse	-	-	60	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	-	270	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	-	300	A
Static chara	acteristics				'	_
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.38	-	V
Dynamic ch	aracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	26	35	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_i = 25 ^{\circ}\text{C}; Fig. 7$	-	35	-	ns

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BYC30B-600P

Hyperfast power diode

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	70	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	nc	no connection	mb	K — A 001aaa020
2	K	cathode[1]		001aaa020
3	Α	anode		
mb	mb	mounting base; connected to cathode	1 3 TO263	

[1] it is not possible to make connection to Pin 2 of the TO263 package

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYC30B-600P	-	Plastic single-ended surface-mounted packaged (D2PAK); 3 leads (one lead cropped) TO263	TO263		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	$δ = 0.5$; $T_{mb} \le 101$ °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	30	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 101 °C; square-wave pulse	-	60	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	270	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	300	Α
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C

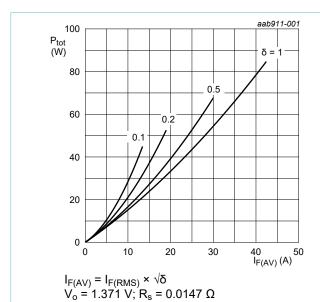


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

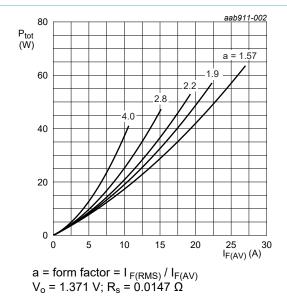
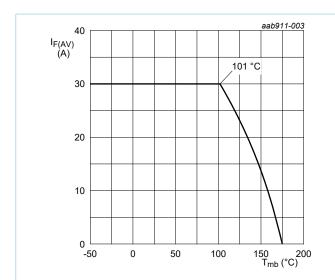


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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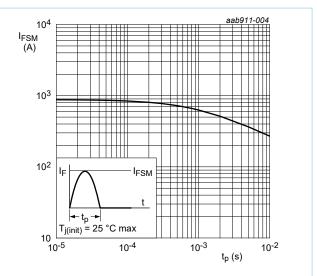


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	1.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W

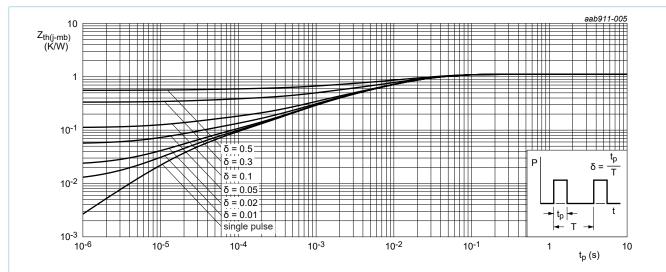


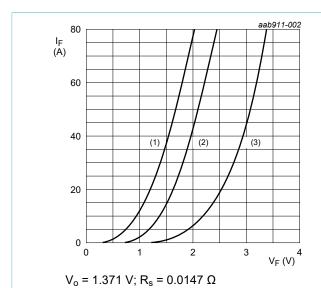
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.38	-	V
I _R	reverse current	$V_R = 600 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	10	μA
		V _R = 600 V; T _j = 125 °C	-	-	500	μA
Dynamic ch	aracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	26	35	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	35	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 \text{ °C}; Fig. 7$	-	70	-	ns
I _{RM}	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}$	-	3.5	-	Α
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}$	-	7.6	-	А
Q _r	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	50	-	nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_i = 125 \text{ °C}; Fig. 7$	-	280	-	nC



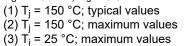


Fig. 6. Forward current as a function of forward voltage

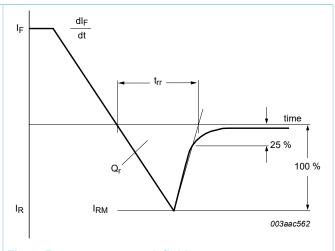
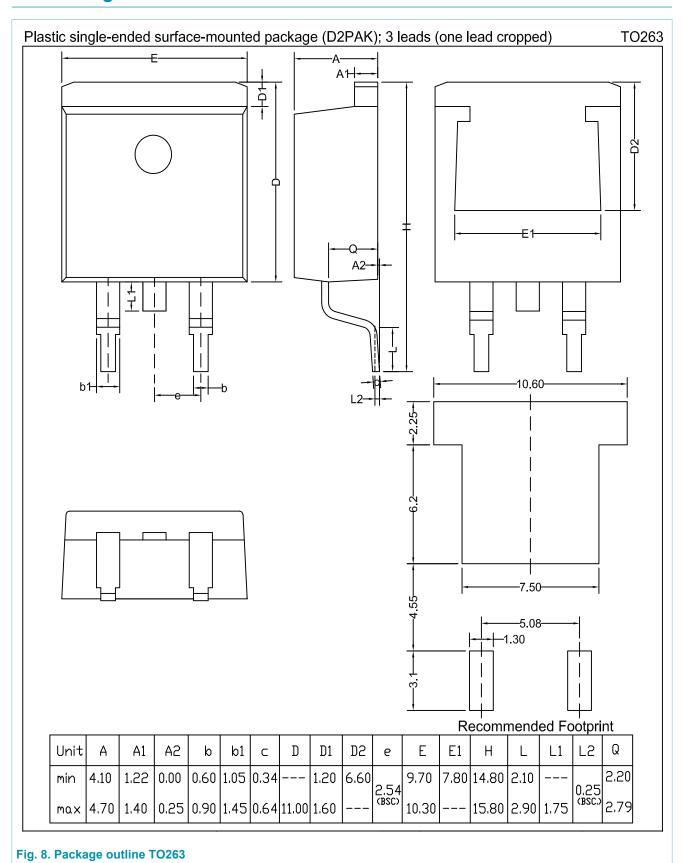


Fig. 7. Reverse recovery definitions; ramp recovery

10. Package outline



11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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